# LMH6622

LMH6622 Dual Wideband, Low Noise, 160MHz, Operational Amplifiers



Literature Number: SNOS986C



### LMH6622

# Dual Wideband, Low Noise, 160MHz, Operational Amplifiers

# **General Description**

The LMH6622 is a dual high speed voltage feedback operational amplifier specifically optimized for low noise. A voltage noise specification of 1.6nV/  $\sqrt{\text{Hz}}$ , a current noise specification 1.5pA/  $\sqrt{\text{Hz}}$ , a bandwidth of 160MHz, and a harmonic distortion specification that exceeds 90dBc combine to make the LMH6622 an ideal choice for the receive channel amplifier in ADSL, VDSL, or other xDSL designs. The LMH6622 operates from  $\pm 2.5 \text{V}$  to  $\pm 6 \text{V}$  in dual supply mode and from  $\pm 5 \text{V}$  to  $\pm 12 \text{V}$  in single supply configuration. The LMH6622 is stable for  $A_{\text{V}} \geq 2$  or  $A_{\text{V}} \leq -1$ . The fabrication of the LMH6622 on National Semiconductor's advanced VIP10 process enables excellent (160MHz) bandwidth at a current consumption of only 4.3mA/amplifier. Packages for this dual amplifier are the 8-lead SOIC and the 8-lead MSOP.

#### **Features**

 $V_S = \pm 6V$ ,  $T_A = 25$ °C, Typical values unless specified

■ Bandwidth  $(A_V = +2)$  160MHz

■ Supply Voltage Range ±2.5V to ±6V +5V to +12

■ Slew rate 85V/µs
■ Supply current 4.3mA/amp

■ Input common mode voltage —4.75V to +5.7V

■ Imput common mode voltage —4.75v to +5.7v
■ Output Voltage Swing (R<sub>L</sub> = 100Ω) ±4.6v

■ Input voltage noise 1.6nV/√Hz

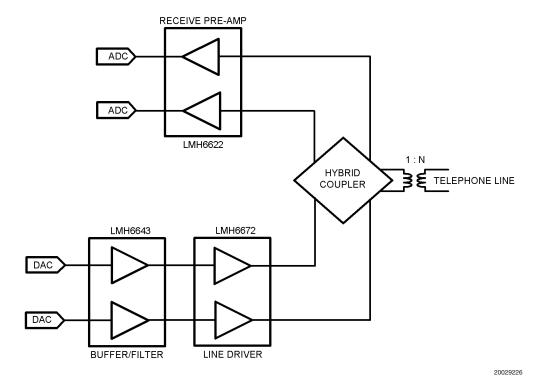
Input current noise
 1.5pA/√Hz
 Linear output current
 90mA

■ Excellent harmonic distortion 90dBc

### **Applications**

- xDSL receiver
- Low noise instrumentation front end
- Ultrasound preamp
- Active filters
- Cellphone basestation

# **xDSL Analog Front End**



## **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

**ESD Tolerance** 

Soldering Information

Infrared or Convection (20 sec) 235°C

Wave Soldering (10 sec) 260°C Storage Temperature Range -65°C to +150°C Junction Temperature (Note 4) +150°C

# **Operating Ratings** (Note 1)

Supply Voltage (V<sup>+</sup>– V<sup>-</sup>)  $\pm 2.25$ V to  $\pm 6$ V Junction Temperature Range  $-40^{\circ}$ C to  $+85^{\circ}$ C

(Note 3), (Note 4)

Package Thermal Resistance (Note 4)  $(\theta_{JA})$ 

8-pin SOIC 166°C/W 8-pin MSOP 211°C/W

### ±6V Electrical Characteristics

Unless otherwise specified,  $T_J = 25^{\circ}C$ ,  $V^+ = 6V$ ,  $V^- = -6V$ ,  $V_{CM} = 0V$ ,  $A_V = +2$ ,  $R_F = 500\Omega$ ,  $R_L = 100\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
Dynamic I	Performance		,	, ,	,	
f <sub>CL</sub>	-3dB BW	$V_O = 200 \text{mV}_{PP}$		160		MHz
BW <sub>0.1dB</sub>	0.1dB Gain Flatness	$V_O = 200 \text{mV}_{PP}$		30		MHz
SR	Slew Rate (Note 8)	$V_O = 2V_{PP}$		85		V/µs
TS	Settling Time	$V_{O} = 2V_{PP}$ to ±0.1%		40		
		$V_{O} = 2V_{PP} \text{ to } \pm 1.0\%$		35		ns
Tr	Rise Time	V <sub>O</sub> = 0.2V Step, 10% to 90%		2.3		ns
Tf	Fall Time	V <sub>O</sub> = 0.2V Step, 10% to 90%		2.3		ns
Distortion	and Noise Response					
e <sub>n</sub>	Input Referred Voltage Noise	f = 100kHz		1.6		nV/ √Hz
i <sub>n</sub>	Input Referred Current Noise	f = 100kHz		1.5		pA/ √Hz
DG	Differential Gain	$R_L = 150\Omega$ , $R_F = 470\Omega$ , NTSC		0.03		%
DP	Differential Phase	$R_L = 150\Omega$ , $R_F = 470\Omega$ , NTSC		0.03		deg
HD2	2 <sup>nd</sup> Harmonic Distortion	$f_c = 1MHz, V_O = 2V_{PP}, R_L = 100\Omega$		-90		dBc
		$f_c = 1MHz, V_O = 2V_{PP}, R_L = 500\Omega$		-100		
HD3	3 <sup>rd</sup> Harmonic Distortion	$f_c = 1MHz, V_O = 2V_{PP}, R_L = 100\Omega$		-94		ID.
		$f_c = 1MHz, V_O = 2V_{PP}, R_L = 500\Omega$		-100		- dBc
MTPR	Upstream	$V_O = 0.6 V_{RMS}$ , 26kHz to 132kHz		-78		
		(see test circuit 5)				dBc
	Downstream	$V_O = 0.6 V_{RMS}$ , 144kHz to 1.1MHz (see test circuit 5)		-70		dbc
Input Cha	racteristics	,		l		
V <sub>os</sub>	Input Offset Voltage	V <sub>CM</sub> = 0V	-1.2	+0.2	+1.2	\/\
			-2		+2	mV
TC V <sub>OS</sub>	Input Offset Average Drift	V <sub>CM</sub> = 0V (Note 7)		-2.5		μV/°C
I <sub>os</sub>	Input Offset Current	V <sub>CM</sub> = 0V	-1	-0.04	1	μΑ
			-1.5		1.5	
I <sub>B</sub>	Input Bias Current	$V_{CM} = 0V$		4.7	10	μΑ
					15	
$R_{IN}$	Input Resistance	Common Mode		17		MΩ
		Differential Mode		12		kΩ
C <sub>IN</sub>	Input Capacitance	Common Mode		0.9		pF
		Differential Mode		1.0		pF

# **±6V Electrical Characteristics** (Continued)

Unless otherwise specified,  $T_J = 25^{\circ}C$ ,  $V^+ = 6V$ ,  $V^- = -6V$ ,  $V_{CM} = 0V$ ,  $A_V = +2$ ,  $R_F = 500\Omega$ ,  $R_L = 100\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
CMVR	Input Common Mode Voltage	CMRR ≥ 60dB		-4.75	-4.5	
	Range		5.5	+5.7		V
CMRR	Common-Mode Rejection Ratio	Input Referred,	80	100		dB
		$V_{CM} = -4.2 \text{ to } +5.2 \text{V}$	75			
Transfer C	Characteristics			•		
A <sub>VOL</sub>	Large Signal Voltage Gain	$V_O = 4V_{PP}$	74 <b>70</b>	83		dB
X <sub>t</sub>	Crosstalk	f = 1MHz		-75		dB
Output Ch	naracteristics		1			
V <sub>O</sub>	Output Swing	No Load, Positive Swing	4.8 <b>4.6</b>	5.2		
		No Load, Negative Swing		-5.0	-4.6 <b>-4.4</b>	
		$R_L = 100\Omega$ , Positive Swing	4.0 <b>3.8</b>	4.6		V
		$R_L = 100\Omega$ , Negative Swing		-4.6	-4 -3.8	
Ro	Output Impedance	f = 1MHz		0.08		Ω
I <sub>SC</sub>	Output Short Circuit Current	Sourcing to Ground $\Delta V_{IN} = 200 mV \text{ (Note 3), (Note 9)}$	100	135		
		Sinking to Ground $\Delta V_{IN} = -200 \text{mV}$ (Note 3), (Note 9)	100	130		mA
I <sub>OUT</sub>	Output Current	Sourcing, $V_O = +4.3V$ Sinking, $V_O = -4.3V$		90		mA
Power Su	pply		-			
+PSRR	Positive Power Supply	Input Referred,	80	95		
	Rejection Ratio	$V_{S} = +5V \text{ to } +6V$	74			dB
-PSRR	Negative Power Supply Rejection Ratio	Input Referred, V <sub>S</sub> = -5V to -6V	75 <b>69</b>	90		иБ
I <sub>S</sub>	Supply Current (per amplifier)	No Load		4.3	6 <b>6.5</b>	mA

### ±2.5V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for  $T_J$  = 25°C,  $V^+$  = 2.5V,  $V^-$  = -2.5V,  $V_{CM}$  = 0V,  $A_V$  = +2,  $R_F$  = 500 $\Omega$ ,  $R_L$  = 100 $\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 6)	(Note 5)	(Note 6)	
Dynamic F	Performance	•				
f <sub>CL</sub>	-3dB BW	$V_O = 200 \text{mV}_{PP}$		150		MHz
BW <sub>0.1dB</sub>	0.1dB Gain Flatness	$V_O = 200 \text{mV}_{PP}$		20		MHz
SR	Slew Rate (Note 8)	$V_O = 2V_{PP}$		80		V/µs
T <sub>S</sub>	Settling Time	$V_{\rm O} = 2V_{\rm PP}$ to ±0.1%		45		20
		$V_{\rm O} = 2V_{\rm PP}$ to ±1.0%		40		ns
T <sub>r</sub>	Rise Time	V <sub>O</sub> = 0.2V Step, 10% to 90%		2.5		ns
T <sub>f</sub>	Fall Time	V <sub>O</sub> = 0.2V Step, 10% to 90%		2.5		ns
Distortion	and Noise Response					
e <sub>n</sub>	Input Referred Voltage Noise	f = 100kHz		1.7		nV/ √Hz
i <sub>n</sub>	Input Referred Current Noise	f = 100kHz		1.5		pA/ √Hz

# **±2.5V Electrical Characteristics** (Continued)

Unless otherwise specified, all limits guaranteed for  $T_J=25^{\circ}C$ ,  $V^+=2.5V$ ,  $V^-=-2.5V$ ,  $V_{CM}=0V$ ,  $A_V=+2$ ,  $R_F=500\Omega$ ,  $R_L=100\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
HD2	2 <sup>nd</sup> Harmonic Distortion	$fc = 1MHz$ , $V_O = 2V_{PP}$ , $R_L = 100\Omega$		-88		
		$fc = 1MHz$ , $V_O = 2V_{PP}$ , $R_L = 500\Omega$		-98		dBc
HD3	3 <sup>rd</sup> Harmonic Distortion	$fc = 1MHz$ , $V_O = 2V_{PP}$ , $R_L = 100\Omega$	00Ω –92			ID.
		$fc = 1MHz$ , $V_O = 2V_{PP}$ , $R_L = 500\Omega$		-100		dBc
MTPR	Upstream	V <sub>O</sub> = 0.4V <sub>RMS</sub> ,26kHz to 132kHz (see test circuit 5)		-76		
	Downstream	$V_O = 0.4V_{RMS}$ ,144kHz to 1.1MHz (see test circuit 5)		-68		- dBc
Input Cha	racteristics	(000 1001 0.10011 0)				1
V <sub>os</sub>	Input Offset Voltage	V <sub>CM</sub> = 0V	-1.5	+0.3	+1.5	
•OS	Impat enest veltage	COM — OF	-2.3	10.0	+2.3	mV
TC V <sub>os</sub>	Input Offset Average Drift	V <sub>CM</sub> = 0V (Note 7)		-2.5		μV/°C
l <sub>os</sub>	Input Offset Current	$V_{CM} = 0V$	-1.5	+0.01	1.5	μA
00			-2.5		2.5	'
I <sub>B</sub>	Input Bias Current	V <sub>CM</sub> = 0V		4.6	10 <b>15</b>	μA
R <sub>IN</sub>	Input Resistance	Common Mode		17		MΩ
IIN		Differential Mode		12		kΩ
C <sub>IN</sub>	Input Capacitance	Common Mode		0.9		pF
- IIV		Differential Mode		1.0		pF
CMVR	Input Common Mode Voltage	CMRR ≥ 60dB		-1.25	-1	<u> </u>
	Range		2	+2.2		V
CMRR	Common Mode Rejection Ratio	Input Referred,	80	100		dB
	Comment mede Hejechen Haue	$V_{CM} = -0.7 \text{ to } +1.7 \text{V}$	75	100		42
Transfer (	L Characteristics	- Civi				
A <sub>VOL</sub>	Large Signal Voltage Gain	$V_O = 1V_{PP}$	74	82		dB
X <sub>t</sub>	Crosstalk	f = 1MHz		-75		dB
	naracteristics					1
V <sub>O</sub>	Output Swing	No Load, Positive Swing	1.4	1.7		
O	3	3	1.2			
		No Load, Negative Swing		-1.5	-1.2 <b>-1</b>	_
		$R_L = 100\Omega$ , Positive Swing	1.2 <b>1</b>	1.5		- V
		$R_L = 100\Omega$ , Negative Swing	· ·	-1.4	-1.1 - <b>0.9</b>	_
R <sub>o</sub>	Output Impedance	f = 1MHz		0.1	3.0	Ω
	Output Short Circuit Current	Sourcing to Ground	100	137		32
I <sub>SC</sub>	Sapat Short Should Suitent	$\Delta V_{IN} = 200 \text{mV} \text{ (Note 3), (Note 9)}$	100	107		
		Sinking to Ground	100	134		mA
				1 .54		
lour	Output Current	$\Delta V_{IN} = -200 \text{mV} \text{ (Note 3), (Note 9)}$		90		mA
I <sub>оит</sub>	Output Current	$\Delta V_{IN} = -200 \text{mV} \text{ (Note 3), (Note 9)}$ Sourcing, $V_O = +0.8 \text{V}$		90		mA
I <sub>OUT</sub>		$\Delta V_{IN} = -200 \text{mV} \text{ (Note 3), (Note 9)}$		90		mA
Power Su	pply	$\Delta V_{IN} = -200 \text{mV}$ (Note 3), (Note 9) Sourcing, $V_O = +0.8 \text{V}$ Sinking, $V_O = -0.8 \text{V}$	78	90		
l <sub>оит</sub> <b>Power Su</b> +PSRR		$\Delta V_{IN} = -200 \text{mV} \text{ (Note 3), (Note 9)}$ Sourcing, $V_O = +0.8 \text{V}$	78 <b>72</b>			mA dB
Power Su	pply Positive Power Supply Rejection	$\Delta V_{IN} = -200 \text{mV} \text{ (Note 3), (Note 9)}$ Sourcing, $V_O = +0.8 \text{V}$ Sinking, $V_O = -0.8 \text{V}$ Input Referred,				

### ±2.5V Electrical Characteristics (Continued)

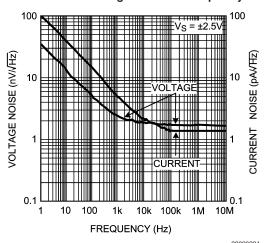
Unless otherwise specified, all limits guaranteed for  $T_J = 25^{\circ}C$ ,  $V^+ = 2.5V$ ,  $V^- = -2.5V$ ,  $V_{CM} = 0V$ ,  $A_V = +2$ ,  $R_F = 500\Omega$ ,  $R_L = 100\Omega$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
			(Note 6)	(Note 5)	(Note 6)	
I <sub>s</sub>	Supply Current (per amplifier)	No Load		4.1	5.8	mA
					6.4	

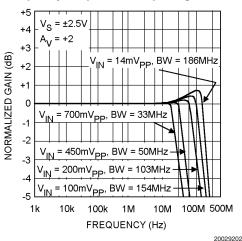
- Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.
- Note 2: Human body model,  $1.5k\Omega$  in series with 100pF. Machine model,  $0\Omega$  in series with 200pF.
- Note 3: Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.
- Note 4: The maximum power dissipation is a function of  $T_{J(MAX)}$ ,  $\theta_{JA}$  and  $T_A$ . The maximum allowable power dissipation at any ambient temperature is  $P_D = (T_{J(MAX)} T_A)/\theta_{JA}$ . All numbers apply for packages soldered directly onto a PC board.
- Note 5: Typical values represent the most likely parametric norm.
- Note 6: All limits are guaranteed by testing or statistical analysis.
- Note 7: Offset voltage average drift is determined by dividing the change in VOS at temperature extremes into the total temperature change.
- Note 8: Slew rate is the slowest of the rising and falling slew rates.
- Note 9: Short circuit test is a momentary test. Output short circuit duration is infinite for  $V_S \le \pm 2.5V$ , at room temperature and below. For  $V_S > \pm 2.5V$ , allowable short circuit duration is 1.5ms.

### **Typical Performance Characteristics**

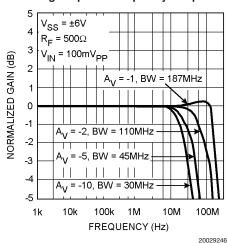
#### **Current and Voltage Noise vs. Frequency**



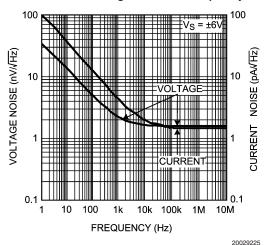
#### Frequency Response vs. Input Signal Level

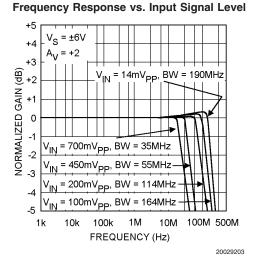


#### **Inverting Amplifier Frequency Response**

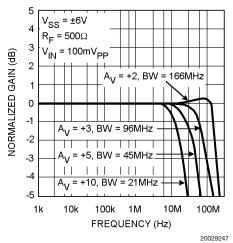


#### Current and Voltage Noise vs. Frequency

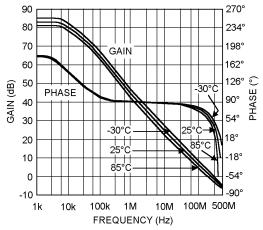




#### **Non-Inverting Amplifier Frequency Response**

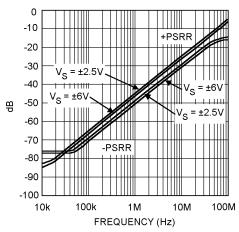


#### Open Loop Gain and Phase Response



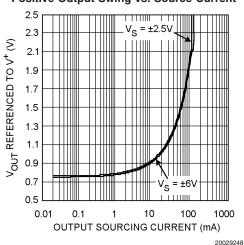
20029205

#### PSRR vs. Frequency

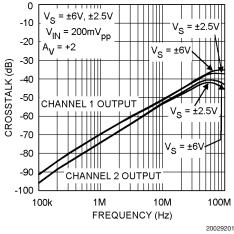


20029204

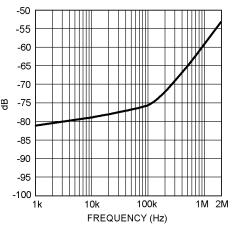
#### Positive Output Swing vs. Source Current



Crosstalk vs. Frequency

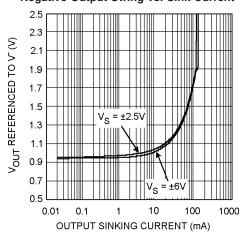


#### CMRR vs. Frequency



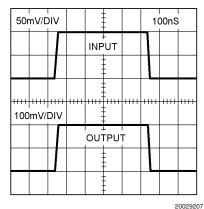
20029206

### **Negative Output Swing vs. Sink Current**

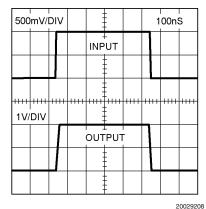


20029249

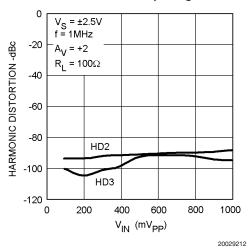
Non-Inverting Small Signal Pulse Response  $V_S$  = ±2.5V,  $R_L$  = 100 $\Omega$ ,  $A_V$  = +2,  $R_F$  = 500 $\Omega$ 



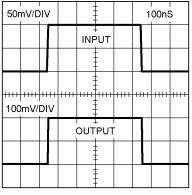
Non-Inverting Large Signal Pulse Response  $V_S = \pm 2.5V$ ,  $R_L = 100\Omega$ ,  $A_V = +2$ ,  $R_F = 500\Omega$ 



Harmonic Distortion vs. Input Signal Level

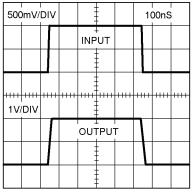


Non-Inverting Small Signal Pulse Response  $V_S = \pm 6V,\, R_L = 100\Omega,\, A_V = +2,\, R_F = 500\Omega$ 



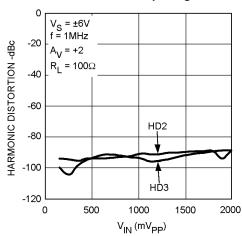
20029209

Non-Inverting Large Signal Pulse Response  $V_S$  = ±6V,  $R_L$  = 100 $\Omega$ ,  $A_V$  = +2,  $R_F$  = 500 $\Omega$ 



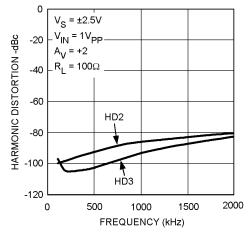
20029210

Harmonic Distortion vs. Input Signal Level



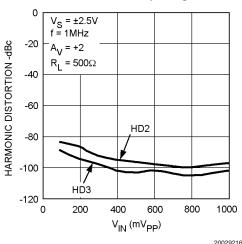
20029213

#### Harmonic Distortion vs. Frequency

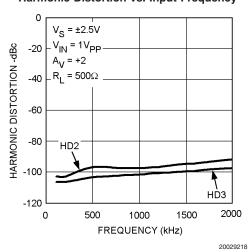


#### 20029214

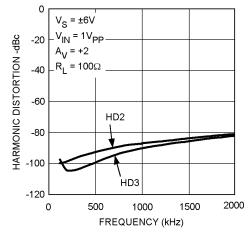
#### Harmonic Distortion vs. Input Signal Level



#### Harmonic Distortion vs. Input Frequency

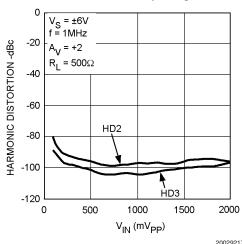


#### Harmonic Distortion vs. Frequency

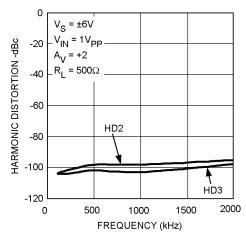


20029215

#### Harmonic Distortion vs. input Signal Level

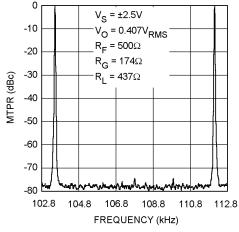


#### **Harmonic Distortion vs. Input Frequency**



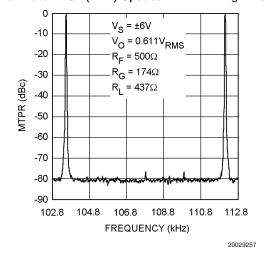
20029219

Full Rate ADSL (DMT) Upstream MTPR @  $V_S = \pm 2.5V$ 

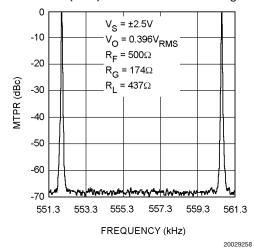


2002925

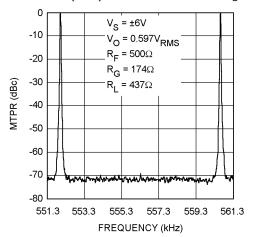
Full Rate ADSL (DMT) Upstream MTPR @  $V_S = \pm 6V$ 



Full Rate ADSL (DMT) Downstream MTPR @  $V_S = \pm 2.5V$ 

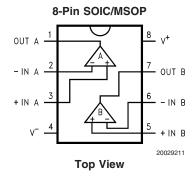


Full Rate ADSL (DMT) Downstream MTPR @ V<sub>S</sub> = ±6V



20029259

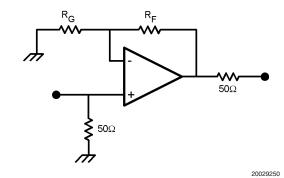
# **Connection Diagram**



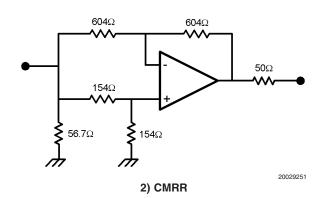
# **Ordering Information**

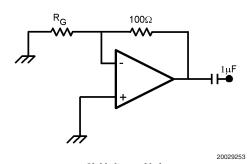
Package	Part Number	Package Marking	Transport Media	NSC Drawing
8-Pin SOIC	LMH6622MA	LMH6622MA	95 Units per Rail	M08A
	LMH6622MAX		2.5k Units Tape and Reel	
8-Pin MSOP	LMH6622MM	A80A 1k Units Tape and Reel		MUA08A
	LMH6622MMX		3.5k Units Tape and Reel	

# **Test Circuits**

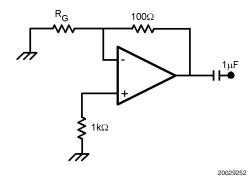


1) Non-Inverting Amplifier



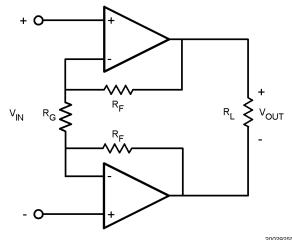


3) Voltage Noise  $\label{eq:RG} \textbf{R}_{\textbf{G}} = \mathbf{1}\Omega \text{ for } \textbf{f} \leq \mathbf{100kHz}, \ \textbf{R}_{\textbf{G}} = \mathbf{20}\Omega \text{ for } \textbf{f} > \mathbf{100kHz}$ 



4) Current Noise  $\rm R_G$  =  $1\Omega$  for f  $\leq 100 kHz, \, R_G$  =  $20\Omega$  for f  $\geq 100 kHz$ 

# Test Circuits (Continued)



5) Multitone Power Ratio,  $R_F = 500\Omega$ ,  $R_G = 174\Omega$ ,  $R_L = 437\Omega$ 

# **DSL Receive Channel Applications**

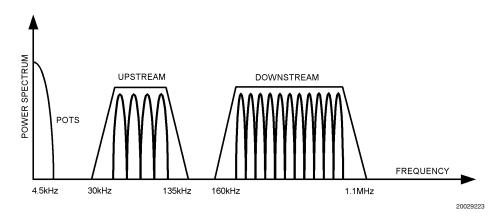


FIGURE 1. ADSL Signal Description

The LMH6622 is a dual, wideband operational amplifier designed for use as a DSL line receiver. In the receive band of a Customer Premises Equipment (CPE) ADSL modem it is possible that as many as 255 Discrete Multi-Tone (DMT) QAM signals will be present, each with its own carrier frequency, modulation, and signal level. The ADSL standard requires a line referred noise power density of -140dBm/Hz within the CPE receive band of 100KHz to 1.1MHz. The CPE driver output signal will leak into the receive path because of full duplex operation and the imperfections of the hybrid coupler circuit. The DSL analog front end must incorporate a

receiver pre-amp which is both low noise and highly linear for ADSL-standard operation. The LMH6622 is designed for the twin performance parameters of low noise and high linearity.

Applications ranging from +5V to +12V or  $\pm 2.5V$  to  $\pm 6V$  are fully supported by the LMH6622. In *Figure 2*, the LMH6622 is used as an inverting summing amplifier to provide both received pre-amp channel gain and driver output signal cancellation, i.e., the function of a hybrid coupler.

# DSL Receive Channel Applications (Continued)

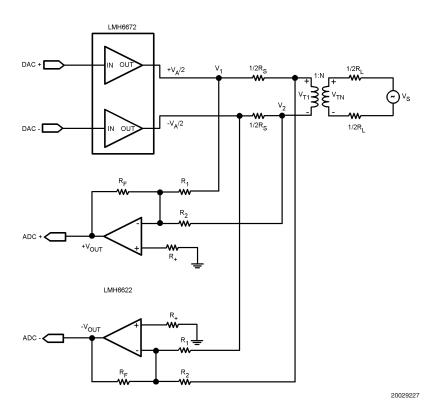


FIGURE 2. ADSL Receive Applications Circuit

# **DSL Receive Channel Applications**

(Continued)

The two  ${\rm R}_{\rm S}$  resistors are used to provide impedance matching through the 1:N transformer.

$$R_S = \frac{R_L}{N^2}$$

Where R<sub>I</sub> is the impedance of the twisted pair line.

N is the turns ratio of the transformer.

The resistors  $R_2$  and  $R_F$  are used to set the receive gain of the pre-amp. The receive gain is selected to meet the ADC full-scale requirement of a DSL chipset.

Resistor  $R_1$  and  $R_2$  along with  $R_F$  are used to achieve cancellation of the output driver signal at the output of the receiver.

Since the LMH6622 is configured as an inverting summing amplifier,  $V_{\text{OUT}}$  is found to be,

$$V_{OUT} = -R_F \left[ \frac{V_1}{R_1} + \frac{V_2}{R_2} \right]$$

The expression for  $V_1$  and  $V_2$  can be found by using superposition principle.

When  $V_S = 0$ ,

$$V_1 = \frac{1}{2}V_A$$
 and  $V_2 = -\frac{1}{4}V_A$ 

When  $V_A = 0$ ,

$$V_1 = 0$$
 and  $V_2 = -\frac{1}{2}V_{T1}$ 

Therefore.

$$V_1 = \frac{1}{2}V_A$$
 and  $V_2 = -\frac{1}{4}V_A - \frac{1}{2}V_{T1}$ 

And then,

$$V_{OUT} = -R_F \left[ \frac{V_A}{2R_1} - \frac{V_A}{4R_2} - \frac{V_{T1}}{2R_2} \right]$$

Setting  $R_1 = 2^*R_2$  to cancel unwanted driver signal in the receive path, then we have

$$V_{OUT} = \frac{R_F}{2R_2} V_{T1}$$

We can also find that,

$$V_{TN} = \frac{1}{2}V_{S}$$
 and  $V_{T1} = \frac{1}{N}V_{TN} = \frac{1}{2N}V_{S}$ 

And then

$$V_{OUT} = \frac{R_F}{4NR_2}V_S$$

In conclusion, the peak-to-peak voltage to the ADC would be,

$$2 V_{OUT} = \frac{R_F}{2NR_2} V_S$$

#### RECEIVE CHANNEL NOISE CALCULATION

The circuit of *Figure 2* also has the characteristic that it cancels noise power from the drive channel.

The noise gain of the receive pre-amp is found to be:

$$A_N = 1 + \frac{R_F}{R_1 / / R_2}$$

Noise power at each of the output of LMH6622:

$$e_{o}^{2} = A_{n}^{2} [V_{n}^{2} + i_{non-inv}^{2} R_{+}^{2} + 4kT R_{+}] + i_{inv}^{2} R_{F}^{2} + 4kT R_{F} A_{n}$$

where

V<sub>n</sub> Input referred voltage noise i<sub>n</sub> Input referred current noise

 $i_{\text{non-inv}}$  Input referred non-inverting current noise  $i_{\text{inv}}$  Input referred inverting current noise k Boltzmann's constant, K = 1.38 x 10<sup>-23</sup>

T Resistor temperature in k

R<sub>+</sub> Source resistance at the non-inverting input to balance offset voltage, typically very small for this inverting summing applications

For a voltage feedback amplifier,

$$i_{inv} = i_{non-inv} = i_{n}$$

Therefore, total output noise from the differential pre-amp is:

$$e^2_{TotalOutput} = 2 e^2_{o}$$

The factor '2' appears here because of differential output.

#### **DIFFERENTIAL ANALOG-TO-DIGITAL DRIVER**

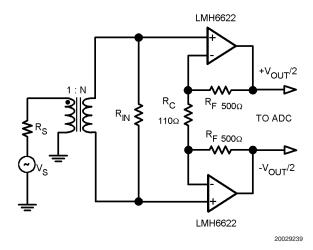


FIGURE 3. Circuit for Differential A/D Driver

### **DSL Receive Channel Applications**

(Continued)

The LMH6622 is a low noise, low distortion high speed operational amplifier. The LMH6622 comes in either SOIC-8 or MSOP-8 packages. Because two channels are available in each package the LMH6622 can be used as a high dynamic range differential amplifier for the purpose of driving a high speed analog-to-digital converter. Driving a 1k $\Omega$  load, the differential amplifier of Figure 3 provides 20dB gain, a flat frequency response up to 6MHz, and harmonic distortion that is lower than 80dBc. This circuit makes use of a transformer to convert a single-ended signal to a differential signal. The input resistor  $R_{\rm IN}$  is chosen by the following equation,

$$R_{IN} = \frac{1}{N^2} R_S$$

The gain of this differential amplifier can be adjusted by  $R_{\text{\scriptsize C}}$  and  $R_{\text{\scriptsize F}},$ 

$$A_V = 2 \frac{R_F}{R_C}$$

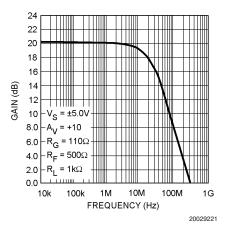


FIGURE 4. Frequency Response

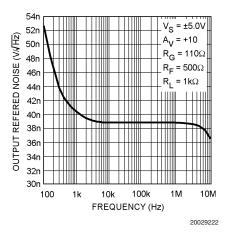


FIGURE 5. Total Output Referred Noise Density

#### CIRCUIT LAYOUT CONSIDERATIONS

National Semiconductor suggests the copper patterns on the evaluation boards listed below as a guide for high frequency layout. These boards are also useful as an aid in device testing and characterization. As is the case with all highspeed amplifiers, accepted-practice R<sub>E</sub> design technique on the PCB layout is mandatory. Generally, a good high frequency layout exhibits a separation of power supply and ground traces from the inverting input and output pins. Parasitic capacitances between these nodes and ground will cause frequency response peaking and possible circuit oscillations (see Application Note OA-15 for more information). High quality chip capacitors with values in the range of 1000pF to 0.1µF should be used for power supply bypassing. One terminal of each chip capacitor is connected to the ground plane and the other terminal is connected to a point that is as close as possible to each supply pin as allowed by the manufacturer's design rules. In addition, a tantalum capacitor with a value between 4.7µF and 10µF should be connected in parallel with the chip capacitor. Signal lines connecting the feedback and gain resistors should be as short as possible to minimize inductance and microstrip line effect. Input and output termination resistors should be placed as close as possible to the input/output pins. Traces greater than 1 inch in length should be impedance matched to the corresponding load termination.

Symmetry between the positive and negative paths in the layout of differential circuitry should be maintained so as to minimize the imbalance of amplitude and phase of the differential signal.

Device	Package	Evaluation Board P/N
LMH6622MA	SOIC-8	CLC730036
LMH6622MM	MSOP-8	CLC730123

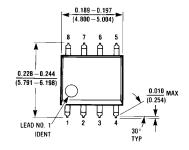
These free evaluation boards are shipped when a device sample request is placed with National Semiconductor.

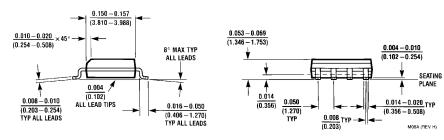
Component value selection is another important parameter in working with high speed/high performance amplifiers. Choosing external resistors that are large in value compared to the value of other critical components will affect the closed loop behavior of the stage because of the interaction of these resistors with parasitic capacitances. These parasitic capacitors could either be inherent to the device or be a by-product of the board layout and component placement. Moreover, a large resistor will also add more thermal noise to the signal path. Either way, keeping the resistor values low will diminish this interaction. On the other hand, choosing very low value resistors could load down nodes and will contribute to higher overall power dissipation and worse distortion.

#### **DRIVING CAPACITIVE LOAD**

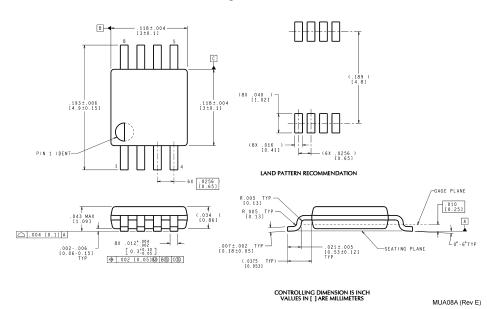
Capacitive Loads decrease the phase margin of all op amps. The output impedance of a feedback amplifier becomes inductive at high frequencies, creating a resonant circuit when the load is capacitive. This can lead to overshoot, ringing and oscillation. To eliminate oscillation or reduce ringing, an isolation resistor can be placed between the load and the output. In general, the bigger the isolation resistor, the more damped the pulse response becomes. For initial evaluation, a  $50\Omega$  isolation resistor is recommended.

# Physical Dimensions inches (millimeters) unless otherwise noted





8-Pin SOIC NS Package Number M08A



8-Pin MSOP NS Package Number MUA08A

#### **Notes**

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.

For the most current product information visit us at www.national.com.

#### LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### **BANNED SUBSTANCE COMPLIANCE**

National Semiconductor manufactures products and uses packing materials that meet the provisions of the Customer Products Stewardship Specification (CSP-9-111C2) and the Banned Substances and Materials of Interest Specification (CSP-9-111S2) and contain no "Banned Substances" as defined in CSP-9-111S2.

Leadfree products are RoHS compliant.



National Semiconductor Americas Customer Support Center

Email: new.feedback@nsc.com Tel: 1-800-272-9959

www.national.com

National Semiconductor
Europe Customer Support Center
Fax: +49 (0) 180-530 85 86
Email: europe.support@nsc.con

Email: europe.support@nsc.com
Deutsch Tel: +49 (0) 69 9508 6208
English Tel: +44 (0) 870 24 0 2171
Français Tel: +33 (0) 1 41 91 8790

National Semiconductor
Asia Pacific Customer
Support Center
Email: ap.support@nsc.com

National Semiconductor Japan Customer Support Center Fax: 81-3-5639-7507 Email: jpn.feedback@nsc.com Tel: 81-3-5639-7560

#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products	Applications
----------	--------------

Audio www.ti.com/audio Communications and Telecom www.ti.com/communications **Amplifiers** amplifier.ti.com Computers and Peripherals www.ti.com/computers dataconverter.ti.com Consumer Electronics www.ti.com/consumer-apps **Data Converters DLP® Products** www.dlp.com **Energy and Lighting** www.ti.com/energy DSP dsp.ti.com Industrial www.ti.com/industrial Clocks and Timers www.ti.com/clocks Medical www.ti.com/medical Interface interface.ti.com Security www.ti.com/security

Logic logic.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Power Mgmt power.ti.com Transportation and Automotive www.ti.com/automotive
Microcontrollers microcontroller.ti.com Video and Imaging www.ti.com/video

RFID <u>www.ti-rfid.com</u>
OMAP Mobile Processors www.ti.com/omap

Wireless Connectivity www.ti.com/wirelessconnectivity

TI E2E Community Home Page e2e.ti.com

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2011, Texas Instruments Incorporated